

■ 表示例 (STDG.M 表示形式)

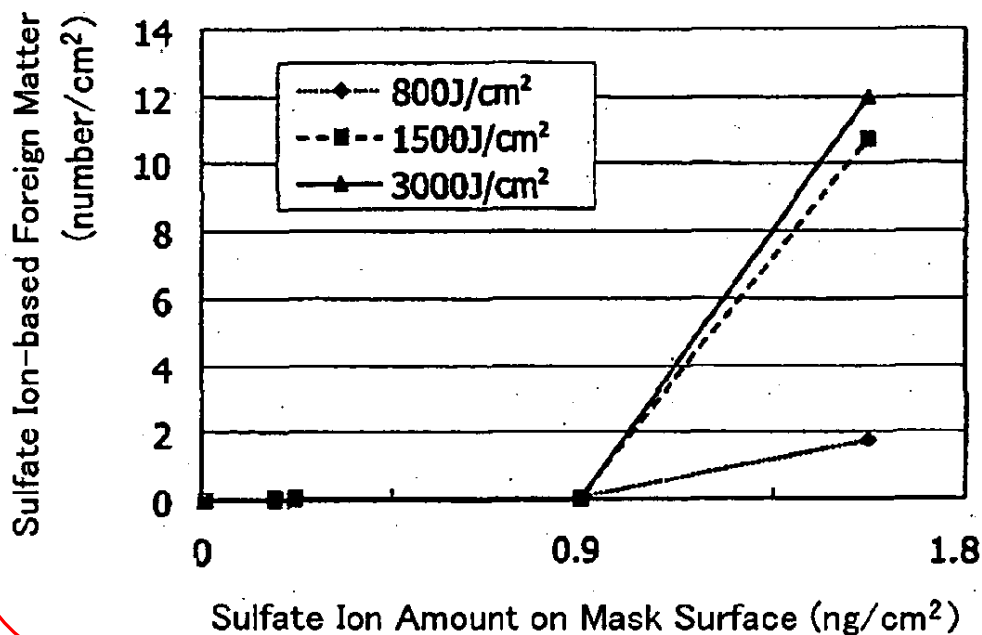
AN 2007:55978 EPFULL EDP 20080227 ED 20080227 UP 20081105 [Full-text](#)  
 DUPD 20081105 DUPW 200845  
 TIEN Method for managing light exposure mask.  
 TIFR Procède pour la gestion d'un masque d'exposition a la lumiere.  
 TIDE Verfahren zur Verwaltung einer Belichtungsmaske.  
 IN Shimada, Shu, Dai Nippon Printing Co., Ltd., 1-1 Ichigaya-Kagacho  
 1-chome, Shinjuku-ku, Tokyo 162-801, JP;  
 Yamamoto, Hideki, Dai Nippon Printing Co., Ltd., 1-1 Ichigaya-Kagacho  
 1-chome, Shinjuku-ku, Tokyo 162-801, JP;  
 Naitoh, Akihiko, Dai Nippon Printing Co., Ltd., 1-1 Ichigaya-Kagacho  
 1-chome, Shinjuku-ku, Tokyo 162-801, JP  
 PA DAI NIPPON PRINTING CO., LTD., 1-1, Ichigaya-Kagacho 1-chome,  
 Shinjuku-ku, Tokyo 162-01, JP  
 PAN 2113198  
 AG Mueller-Bore & Partner Patentanwaelte, Grafinger Strasse 2, 81671  
 Muenchen, DE  
 AGN 100651  
 DT Patent  
 LAF English  
 LA English  
 LAP English  
 TL German; English; French  
 PIT EPA1 Application published with search report  
 PI EP 1892571 A1 20080227  
 DS DE FR IT  
 AI EP 2007-16206 A 20070817  
 PRAI JP 2006-225467 A 20060822  
 RECA 4. THERE ARE 4 CITED AUTHOR REFERENCES (3 PATENT, 1 NON PATENT)  
 AVAILABLE FOR THIS RECORD. ALL CITATIONS ARE AVAILABLE IN THE RE FORMAT.  
 IPCI G03F0001-00 [I,A]  
 G03F0001-00 [I,C\*]

発明者引用 (公開公報)  
 特許 3 件  
 非特許文献 1 件

イメージ表示 (GI)

<imgaf001>

FIG. 1



AN 2007:55978 EPFULL EDP 20080227 ED 20090325 UP 20090325 [Full-text](#)  
 DUPD 20090325 DUPW 200913

TIEN Method for managing light exposure mask.  
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 TIDE Verfahren zur Verwaltung einer Belichtungsmaske.

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PAN 2113198

AG Mueller-Bore & Partner Patentanwaelte, Grafinger Strasse 2, 81671  
 Muenchen, DE

AGN 100651

DT Patent

LAF English

LA English

LAP English

TL German; English; French

PIT EPB1 Granted patent

PI EP 1892571 B1 20090325

DS DE FR IT

AI EP 2007-16206 A 20070817

PRAI JP 2006-225467 A 20060822

REP EP 1341042 A (INID56)  
 US 20060019177 A1 (INID56)

REN (1) BHATTACHARYYA K ET AL: "Investigation of reticle defect formation at  
 DUV lithography" 2003 PROCEEDINGS IEEE/SEMI ADVANCED SEMICONDUCTOR  
 MANUFACTURING CONFERENCE AND WORKSHOP. (ASMC). MUNICH, GERMANY, MARCH 31  
 - APRIL 1, 2003, IEEE/SEMI ADVANCED SEMICONDUCTOR MANUFACTURING  
 CONFERENCE AND WORKSHOP, NEW YORK, NY : IEEE, US, 31 March 2003  
 (2003-03-31), pages 29-35, XP010747111 ISBN: 0-7803-7673-0 (INID56)  
 (2) GRENON B J ET AL: "Reticle surface contaminants and their  
 relationship to sub-pellicle defect formation" PROCEEDINGS OF THE SPIE -  
 THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING SPIE-INT. SOC. OPT.  
 ENG USA, vol. 5375, no. 1, 24 May 2004 (2004-05-24), pages 355-362,  
 XP002453361 ISSN: 0277-786X (INID56)  
 (3) SCHMID R ET AL: "Evaluation of printability of crystal growth  
 defects in a 193nm lithography environment using AIMS" PROCEEDINGS OF  
 THE SPIE - THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING SPIE-INT.  
 SOC. OPT. ENG USA, vol. 5567, no. 1, 2004, pages 1035-1043, XP002453362  
 ISSN: 0277-786X (INID56)

RECA 6. THERE ARE 6 CITED AUTHOR REFERENCES (4 PATENT, 2 NON PATENT)  
 AVAILABLE FOR THIS RECORD. ALL CITATIONS ARE AVAILABLE IN THE RE FORMAT.

IPC1 G03F0001-00 [I,A]  
 G03F0001-00 [I,C\*]

発明者引用 (登録公報) 特許 4 件 非特許文献 2 件
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■ 表示例 (RE.M 表示形式)

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 JP 2004053817 A (APP) [0003]  
 JP 2005308896 A (APP) [0005]

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 発明者引用情報

RENA (1) H. HABUKA et al., Jpn. J. Appl. Phys. , 20030000, volume 42, pages 1575 (APP) [0028]

REP EP 1341042 A (INID56)  
 US 20060019177 A1 (INID56)

REN (1) BHATTACHARYYA K ET AL: "Investigation of reticle defect formation at DUV lithography" 2003 PROCEEDINGS IEEE/SEMI ADVANCED SEMICONDUCTOR MANUFACTURING CONFERENCE AND WORKSHOP. (ASMC). MUNICH, GERMANY, MARCH 31 - APRIL 1, 2003, IEEE/SEMI ADVANCED SEMICONDUCTOR MANUFACTURING CONFERENCE AND WORKSHOP, NEW YORK, NY : IEEE, US, 31 March 2003 (2003-03-31), pages 29-35, XP010747111 ISBN: 0-7803-7673-0 (INID56)  
 (2) GRENON B J ET AL: "Reticle surface contaminants and their relationship to sub-pellicle defect formation" PROCEEDINGS OF THE SPIE - THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING SPIE-INT. SOC. OPT. ENG USA, vol. 5375, no. 1, 24 May 2004 (2004-05-24), pages 355-362, XP002453361 ISSN: 0277-786X (INID56)  
 (3) SCHMID R ET AL: "Evaluation of printability of crystal growth defects in a 193nm lithography environment using AIMS" PROCEEDINGS OF THE SPIE - THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING SPIE-INT. SOC. OPT. ENG USA, vol. 5567, no. 1, 2004, pages 1035-1043, XP002453362 ISSN: 0277-786X (INID56)

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 審査官およびサーチ  
 レポートの引用情報

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 JP 2005308896 A (APP) [0005]  
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 発明者引用情報

RENA (1) BHATTACHARYYA et al., Investigation of reticle defect formation at DUV lithography, 14h Annual IEEE/SEMI Advanced Semiconductor Manufacturing Conference and Workshop , 20030000, pages 29-35 (APP) [0003]  
 (2) H. HABUKA et al., Jpn. J. Appl. Phys. , 20030000, volume 42, pages 1575 (APP) [0029]